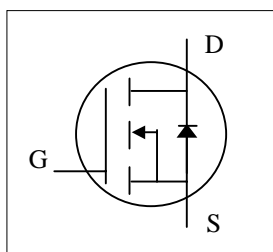
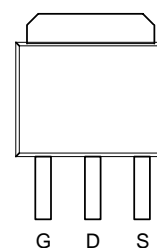




- ▼ 100% R_g & UIS Test
- ▼ Fast Switching Characteristic
- ▼ Simple Drive Requirement
- ▼ RoHS Compliant & Halogen-Free



BV_{DSS}	700V
$R_{DS(ON)}$	1.4 Ω
I_D^3	3.2A



TO-251S(JB)

Description

AP70SL1K4B series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The TO-251S short lead package is preferred for all commercial-industrial through-hole applications without lead-cuttred.

Absolute Maximum Ratings @T_j=25°C (unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	700	V
V_{GS}	Gate-Source Voltage	± 20	V
V_{GS}	Gate-Source Voltage, AC (f > 1Hz)	± 30	V
$I_D @ T_C=25^\circ C$	Drain Current, $V_{GS} @ 10V^3$	3.2	A
$I_D @ T_C=100^\circ C$	Drain Current, $V_{GS} @ 10V^3$	2.1	A
I_{DM}	Pulsed Drain Current ¹	8.3	A
dv/dt	MOSFET dv/dt Ruggedness ($V_{DS} = 0 \dots 400V$)	20	V/ns
$P_D @ T_C=25^\circ C$	Total Power Dissipation	28.4	W
$P_D @ T_A=25^\circ C$	Total Power Dissipation	1.13	W
E_{AS}	Single Pulse Avalanche Energy ⁴	27	mJ
I_{AR}	Avalanche Current	0.6	A
E_{AR}	Repetitive Avalanche Energy	2.84	mJ
dv/dt	Peak Diode Recovery dv/dt ⁵	15	V/ns
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Maximum Thermal Resistance, Junction-case	4.4	°C/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient	110	°C/W



AP70SL1K4BJB

Electrical Characteristics @T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	700	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =1A	-	-	1.4	Ω
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	2	-	5	V
I _{D(ON)}	On State Drain Current	V _{GS} =10V, V _{DS} =20V	5	-	-	A
g _{fs}	Forward Transconductance	V _{DS} =20V, I _D =1A	-	2.4	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =560V, V _{GS} =0V	-	-	100	uA
	Drain-Source Leakage Current(T _J =150°C)	V _{DS} =560V, V _{GS} =0V	-	-	500	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V, V _{DS} =0V	-	-	±1	uA
Q _g	Total Gate Charge	I _D =1.5A	-	11.2	18	nC
Q _{gs}	Gate-Source Charge	V _{DS} =480V	-	3	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =10V	-	5	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =400V	-	11	-	ns
t _r	Rise Time	I _D =1.5A	-	9	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =10Ω	-	27	-	ns
t _f	Fall Time	V _{GS} =10V	-	15	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	380	608	pF
C _{oss}	Output Capacitance	V _{DS} =100V	-	15	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	6	-	pF
R _g	Gate Resistance	f=1.0MHz	-	12	24	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
I _S	Source Current (Body Diode)	T _C =25°C	-	-	3.2	A
V _{SD}	Forward On Voltage ²	I _S =1.5A, V _{GS} =0V	-	0.8	-	V
t _{rr}	Reverse Recovery Time	I _S =1.5, V _{GS} =0V	-	130	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt=100A/μs	-	610	-	nC

Notes:

- 1.Pulse width limited by max. junction temperature.
- 2.Pulse test
- 3.Limited by max. junction temperature. Maximum duty cycle D=0.75
- 4.Starting T_J=25°C , V_{DD}=50V , L=150mH , R_G=25Ω
- 5.I_{SD} ≤ I_D, V_{DD} ≤ BV_{DSS}, starting T_J = 25°C

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

APEC RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.

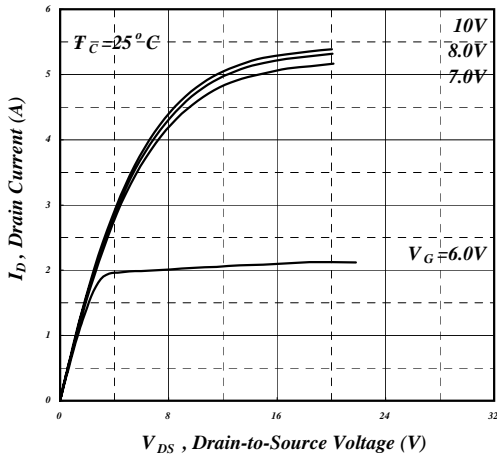


Fig 1. Typical Output Characteristics

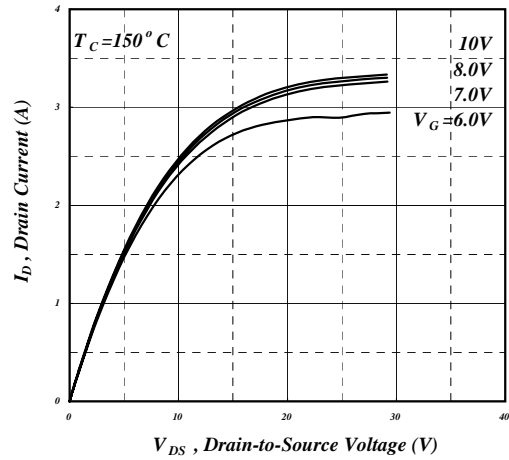


Fig 2. Typical Output Characteristics

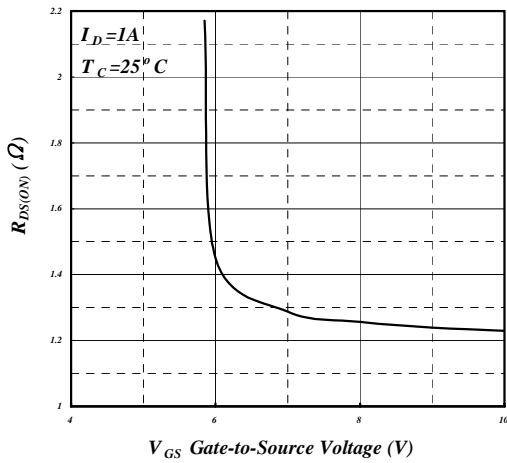


Fig 3. On-Resistance v.s. Gate Voltage

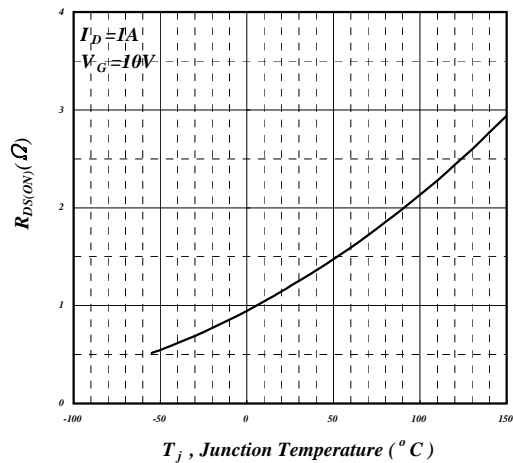


Fig 4. Static On-Resistance v.s. Junction Temperature

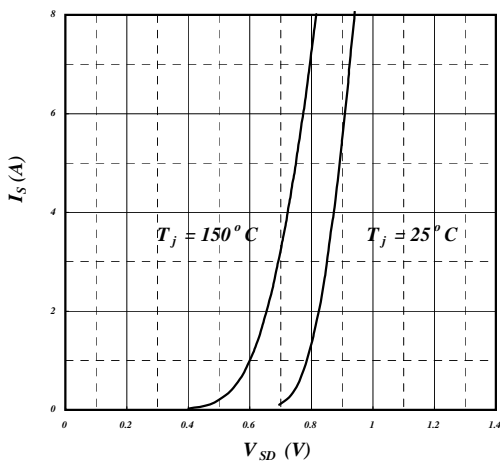


Fig 5. Forward Characteristic of Reverse Diode

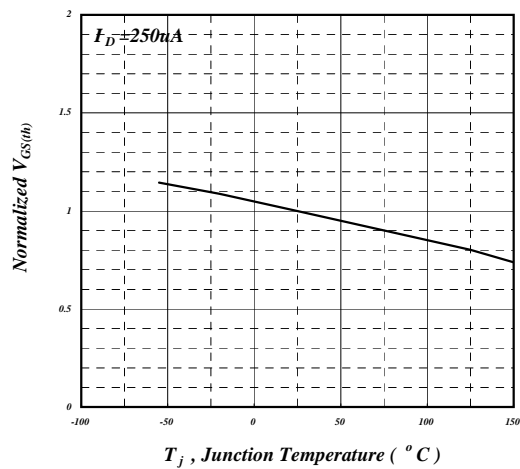


Fig 6. Gate Threshold Voltage v.s. Junction Temperature

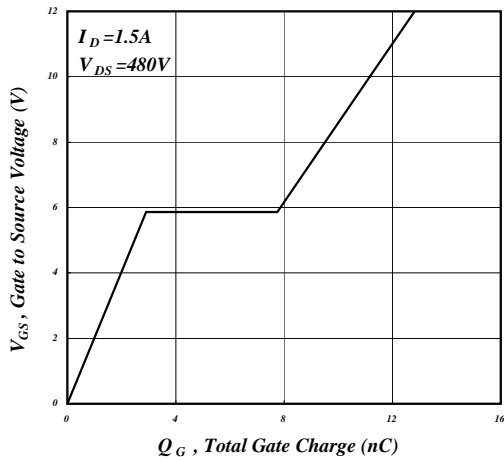


Fig 7. Gate Charge Characteristics

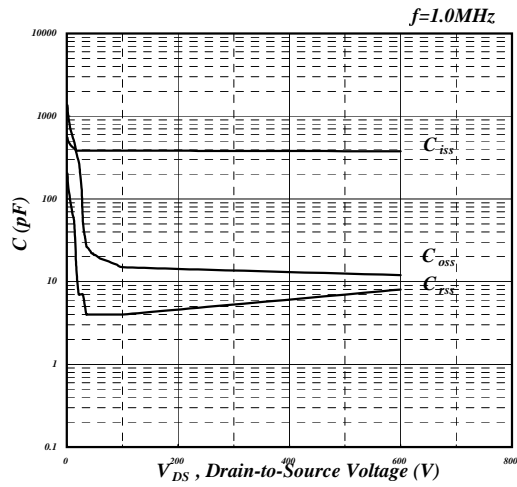


Fig 8. Typical Capacitance Characteristics

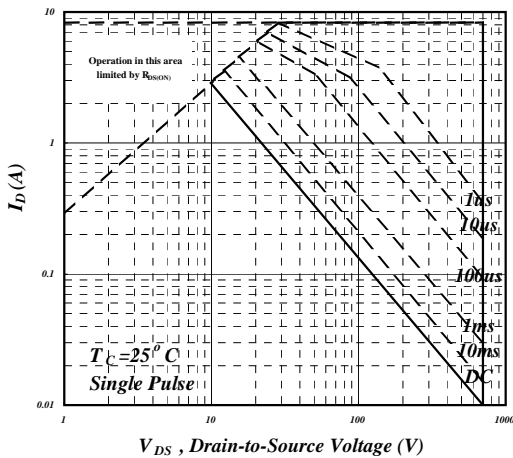


Fig 9. Maximum Safe Operating Area

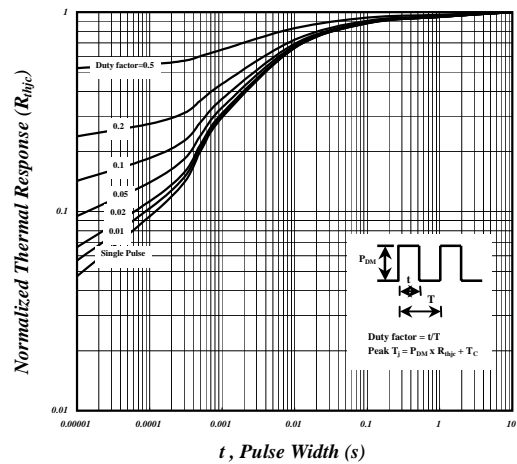


Fig 10. Effective Transient Thermal Impedance

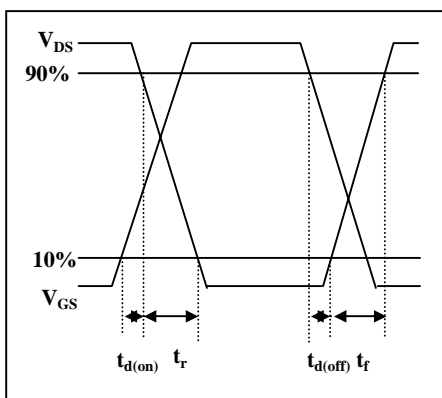


Fig 11. Switching Time Waveform

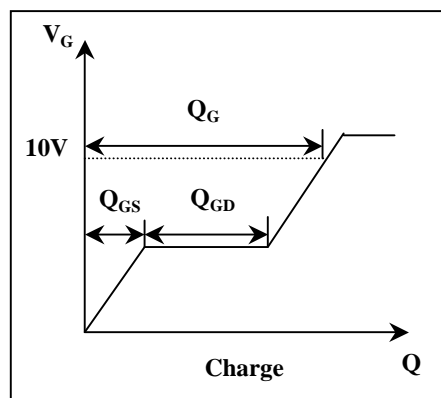


Fig 12. Gate Charge Waveform

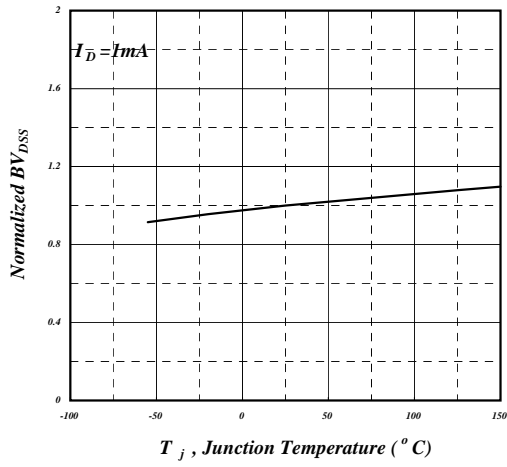


Fig 13. Normalized BV_{DSS} v.s. Junction Temperature

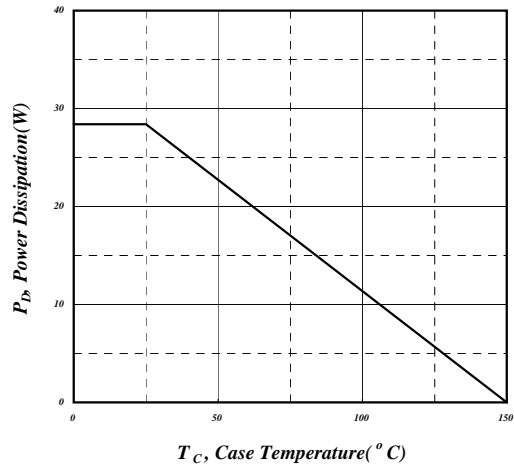


Fig 14. Total Power Dissipation

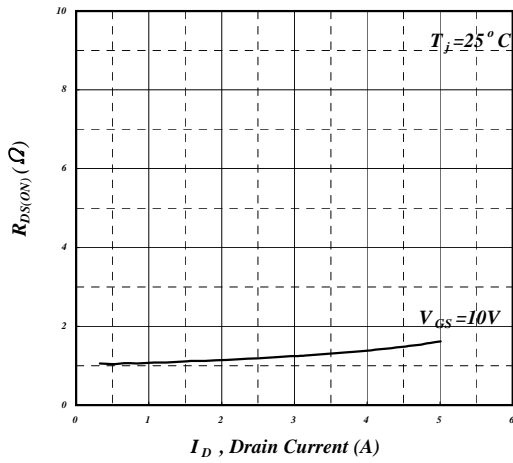


Fig 15. Typ. Drain-Source on State Resistance

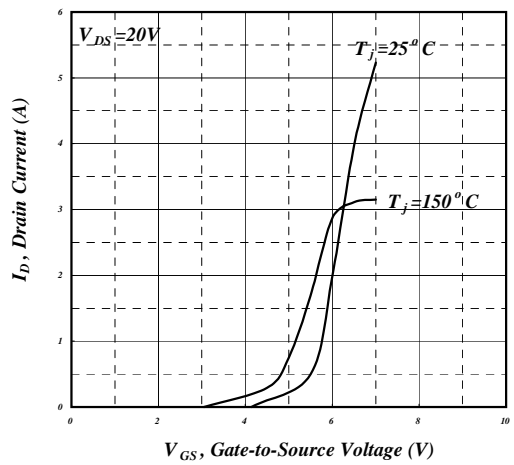
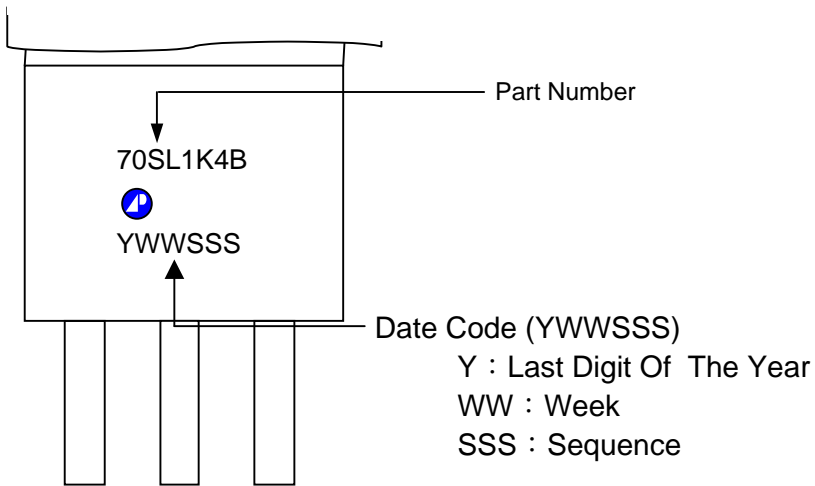


Fig 16. Transfer Characteristics



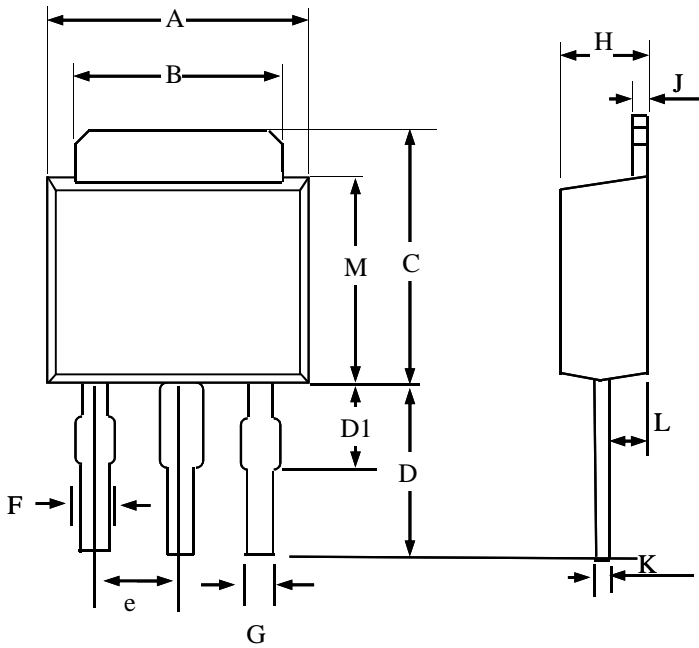
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MARKING INFORMATION





Package Outline : TO-251S



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	6.30	6.55	6.80
B	4.90	5.20	5.50
C	6.80	7.30	7.80
D	3.00		4.50
e	2.30 REF.		
F	0.60	0.90	1.20
G	0.50	0.70	0.90
H	2.10	2.25	2.40
J	0.40	0.50	0.60
K	0.40	0.50	0.60
L	0.90	1.20	1.50
M	5.40	5.90	6.40
D1	0.90	1.35	1.80

- 1.All Dimensions Are in Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.



TO-251S FOOTPRINT :

